

May 2009

## FDG6317NZ

# Dual 20v N-Channel PowerTrench MOSFET

### **General Description**

This dual N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized use in small switching regulators, providing an extremely low R<sub>DS(ON)</sub> and gate charge (Q<sub>G</sub>) in a small package.

### **Applications**

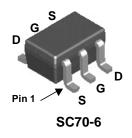
- · DC/DC converter
- · Power management
- Load switch
- · RoHS Compliant

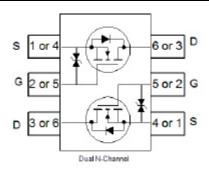


**Features** 

- 0.7 A, 20 V.  $R_{DS(ON)}$  = 400 m $\Omega$  @  $V_{GS}$  = 4.5 V  $R_{DS(ON)} = 550 \text{ m}\Omega @ V_{GS} = 2.5 \text{ V}$
- · Gate-Source Zener for ESD ruggedness (1.6kV Human Body Model). (Note 3)
- · Low gate charge
- High performance trench technology for extremely
- Compact industry standard SC70-6 surface mount package







The pinouts are symmetrical; pin 1 and pin 4 are interchangeable.

## Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		20	V
V <sub>GSS</sub>	Gate-Source Voltage		± 12	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1)	0.7	Α
	– Pulsed		2.1	
P <sub>D</sub>	Power Dissipation for Single Operation	(Note 1)	0.3	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperati	ure Range	-55 to +150	°C

### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1)	415	°C/W
-----------------	---	----------	-----	------

**Package Marking and Ordering Information** 

Device Marking	Device	Reel Size	Tape width	Quantity
.67	FDG6317NZ	7"	8mm	3000 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV <sub>DSS</sub>	Drain–Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \qquad I_{D} = 250 \mu\text{A}$	20			V
ΔBV <sub>DSS</sub> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		13		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 16 V, V <sub>GS</sub> = 0 V			1	μΑ
I <sub>GSS</sub>	Gate-Body Leakage	$V_{GS} = \pm 12 \text{ V}, \ V_{DS} = 0 \text{ V}$			± 10	μΑ
I <sub>GSS</sub>	Gate-Body Leakage	$V_{GS} = \pm 4.5 \text{ V}, V_{DS} = 0 \text{ V}$			± 1	μΑ
On Char	acteristics (Note 2)			•	•	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.6	1.2	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D$ = -250 $\mu$ A, Referenced to 25°C		-2		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source On–Resistance	$V_{GS} = 4.5 \text{ V},  I_D = 0.7 \text{ A}$ $V_{GS} = 2.5 \text{ V},  I_D = 0.6 \text{ A}$ $V_{GS} = 4.5 \text{ V},  I_D = 0.7 \text{ A}, T_J = 125 ^{\circ}\text{C}$		300 450 390	400 550 560	mΩ
I <sub>D(on)</sub>	On–State Drain Current	$V_{GS} = 4.5 \text{ V},  V_{DS} = 5 \text{ V}$	1			Α
<b>g</b> <sub>FS</sub>	Forward Transconductance	$V_{DS} = 5 \text{ V}, \qquad I_{D} = 0.7 \text{ A}$		1.8		S
Dynamic	Characteristics		•			
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V,		66.5		pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		19		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			10		pF
$R_G$	Gate Resistance	$V_{GS} = 15 \text{ mV}, f = 1.0 \text{ MHz}$		5.8		Ω
Switching	Characteristics (Note 2)					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 10 \text{ V},  I_{D} = 1 \text{ A},$		5.5	11	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = 4.5 \text{ V},  R_{GEN} = 6 \Omega$		7	15	ns
$t_{d(off)}$	Turn-Off Delay Time			7.5	15	ns
t <sub>f</sub>	Turn-Off Fall Time			2.5	5	ns
Qg	Total Gate Charge	$V_{DS} = 10 \text{ V},  I_{D} = 0.7 \text{ A},$		0.76	1.1	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 4.5 V		0.18		nC
$Q_{gd}$	Gate-Drain Charge			0.20		nC
Drain-So	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Sour	<del>_</del>			0.25	Α
$V_{\text{SD}}$	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \qquad I_S = 0.25 \text{ A (Note 2)}$		0.8	1.2	V
t <sub>rr</sub>	Diode Reverse Recovery Time	$I_F = 0.7 \text{ A}, \qquad d_{iF}/d_t = 100 \text{ A}/\mu\text{s}$		8.3		nS
Q <sub>rr</sub>	Diode Reverse Recovery Charge			1.2		nC

#### Notes

<sup>1.</sup>  $R_{8JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{8JC}$  is guaranteed by design while  $R_{8JA}$  is determined by the user's board design.  $R_{8JA}$  = 415°C/W when mounted on a minimum pad .

<sup>2.</sup> Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

<sup>3.</sup> The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

## **Typical Characteristics**

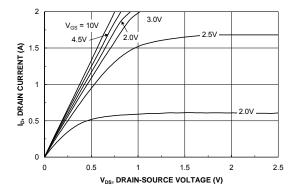


Figure 1. On-Region Characteristics.

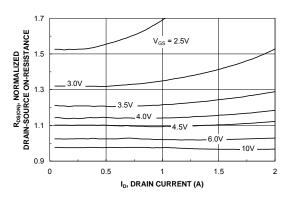


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

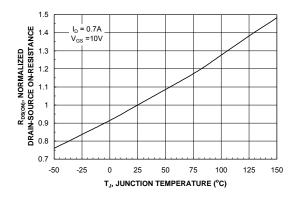


Figure 3. On-Resistance Variation with Temperature.

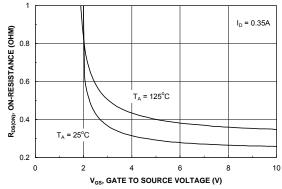


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

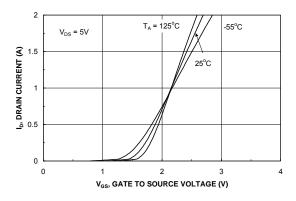


Figure 5. Transfer Characteristics.

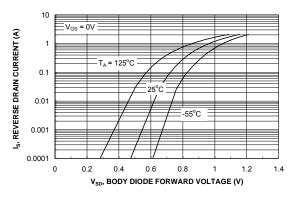


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

f = 1MHz

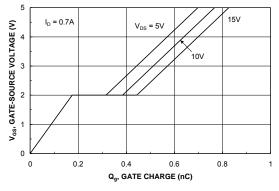
 $V_{GS} = 0 V$ 

20

 $C_{iss}$ 

15

## **Typical Characteristics**



25  $C_{\text{rss}}$ 0 0 10 V<sub>DS</sub>, DRAIN TO SOURCE VOLTAGE (V)

100

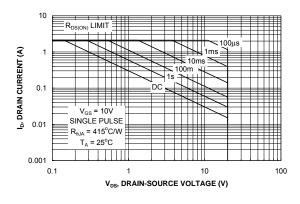
CAPACITANCE (pF)

50

Figure 7. Gate Charge Characteristics.



 $\mathsf{C}_{\mathsf{oss}}$ 



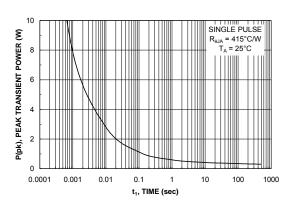


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

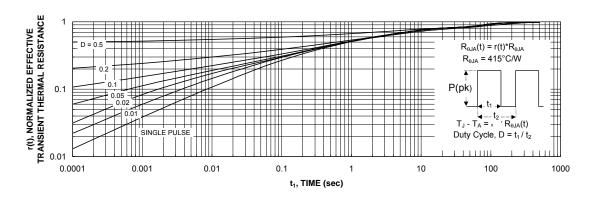


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1. Transient thermal response will change depending on the circuit board design.





#### TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

Auto-SPM™ Build it Now™ CorePLUS™ CorePOWER™  $CROSSVOLT^{\text{TM}}$ Current Transfer Logic™

EcoSPARK® EfficentMax™ EZSWITCH™ \*

airchild®

Fairchild Semiconductor® FACT Quiet Series™

FACT<sup>®</sup> FAST® FastvCore<sup>™</sup> FETBench™ FlashWriter® \*

F-PFS™ FRFET®

Global Power Resource<sup>SM</sup> Green FPS™ Green FPS™ e-Series™

Gmax™ GTO™ IntelliMAX™ ISOPLANAR™ MegaBuck™ MIČROCOUPLER™

MicroFET™ MicroPak™ MillerDrive™ MotionMax™ Motion-SPM™ OPTOLOGIC® OPTOPLANAR®

PDP SPM™ Power-SPM™ PowerTrench<sup>®</sup> PowerXS™

Programmable Active Droop™

**OFET®** QS<sup>TM</sup> Quiet Series™ RapidConfigure™

Saving our world, 1mW /W /kW at a time™ SmartMax™

SMART START™ SPM® STEALTH™ SuperFET™ SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SupreMOS™ SyncFET™ Sync-Lock™

SYSTEM ®

The Power Franchise® bwer' ا TinyBoost™

TinyBuck™ TinyLogic<sup>®</sup> TINYOPTO™ TinvPower™ TinyPWM™ TinyWire™ TriFault Detect™ TRUECURRENT\*\*\* μSerDes™

**UHC®** Ultra FRFET™ UniFET™ VCX™ VisualMax™ XSTM

\*Trademarks of System General Corporation, used under license by Fairchild Semiconductor

#### DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY
FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness

#### ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

#### PRODUCT STATUS DEFINITIONS **Definition of Terms**

Datasheet Identification Product Status		Definition		
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.		
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.		
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.		
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.		

Rev. I40

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Fairchild Semiconductor: FDG6317NZ